

ABSTRACT OF THE DISCLOSURE

A semiconductor device and a process for production thereof, said semiconductor device having a new electrode structure which has a low resistivity and withstands heat treatment at 400°C and above. Heat treatment at a high temperature (400-700°C) is possible because the wiring is made of Ta film or Ta-based film having high heat resistance. This heat treatment permits the gettering of metal element in crystalline silicon film. Since this heat treatment is lower than the temperature which the gate wiring (0.1-5 μm wide) withstands and the gate wiring is protected with a protective film, the gate wiring retains its low resistance.